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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/026,760	12/27/2001	Byoung Ho Lim	049128-5053	9786
9629	7590	04/05/2005	EXAMINER	
MORGAN LEWIS & BOCKIUS LLP 1111 PENNSYLVANIA AVENUE NW WASHINGTON, DC 20004			LANDAU, MATTHEW C	
			ART UNIT	PAPER NUMBER

2815

DATE MAILED: 04/05/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

# Office Action Summary

Application No.

10/026,760

Applicant(s)

LIM, BYOUNG HO

Examiner

Matthew Landau

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

## Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

## Status

- 1) ☒ Responsive to communication(s) filed on 28 February 2005.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

## Disposition of Claims

- 4) ☒ Claim(s) 1-21 is/are pending in the application.
- 4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.
- 5) ☐ Claim(s) \_\_\_\_\_ is/are allowed.
- 6) ☒ Claim(s) 1-21 is/are rejected.
- 7) ☐ Claim(s) \_\_\_\_\_ is/are objected to.
- 8) ☐ Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

## Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on \_\_\_\_\_ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.  
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).  
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

## Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some \* c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- \* See the attached detailed Office action for a list of the certified copies not received.

## Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)  
Paper No(s)/Mail Date \_\_\_\_\_
- 4) ☐ Interview Summary (PTO-413)  
Paper No(s)/Mail Date. \_\_\_\_\_
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: \_\_\_\_\_

## DETAILED ACTION

### *Claim Rejections - 35 USC § 102*

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1, 10, 13, and 21 are rejected under 35 U.S.C. 102(b) as being anticipated by Shin (US Pat. 5,766,493).

Regarding claims 1, 10, 13, and 21, Figures 3A-3E of Shin disclose a method of fabricating a liquid crystal display panel comprising the steps of: preparing an upper substrate 20 and a lower substrate 10; bonding the upper substrate to the lower substrate; cleaning exposed surfaces of the bonded upper and lower substrates to removed foreign materials formed on the lower substrate during the preparing of the lower substrate; and simultaneously eliminating the cleaned exposed surfaces of the bonded upper and lower substrates, wherein a thickness of the panel is uniformly reduced. Note that Shin's disclosed step of preparing the lower substrate (including forming a TFT, pixel electrode, scanning line and data line) (col. 3, lines 53-57) will result in at least some type of impurity/foreign material adhering to the exposed surface of the lower substrate 10. Shin discloses the step of eliminating the exposed surfaces can be done physically (with sandpaper or polishing device) (col. 4, lines 22-24). Therefore, any foreign materials on the surface of the substrates will be physically removed just prior to the removal of the exposed substrate surfaces.

***Claim Rejections - 35 USC § 103***

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 1, 3-10, 12-14, and 16-21 are rejected under 35 U.S.C. 103(a) as being unpatentable over the admitted prior art (APA) in view of Matsushima.

Regarding claims 1, 3, 10, 12-14, 16, 20, and 21, Figures 2A-F and Figure 3 of this instant application discloses a method of fabricating a liquid crystal display panel, comprising the steps of: preparing an upper substrate 28 and a lower substrate 18; forming a gate electrode 15 on the lower substrate 18; forming a gate insulating film 19 on the lower substrate to cover the gate electrode; forming an active layer 21 on the gate insulating film; and forming a source electrode 13 and a drain electrode 11 on the active layer; and bonding an upper substrate 28 to a lower substrate 18. Figure 3 of the APA also discloses foreign materials 25A formed on the lower substrate during the preparing of the lower substrate. The difference between the APA and the claimed invention is the steps of cleaning the exposed surfaces of the bonded upper and lower substrates to remove the foreign materials and simultaneously eliminating/removing the cleaned exposed surfaces of the bonded upper and lower substrates. Matsushima discloses a method of fabricating an LCD panel including wet-etching the exposed surfaces of bonded upper and lower substrates (100a and 101a, respectively) (col. 8, lines 26-36). Furthermore, since the upper and lower substrates (100a and 101a, respectively) are bonded prior to be immersed in an etching tank, exposed surfaces of both substrates are eliminated simultaneously and the thickness

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of the LCD panel is reduced uniformly. In view of such teaching, it would have been obvious to the ordinary artisan at the time the invention was made to modify the invention of the APA by using the etching process of Matsushima for the purpose of reducing the total weight of the substrates and obtaining a smooth surface. Note that it is inherent that at least some of the foreign materials on the lower substrate will be removed when the bonded upper and lower substrates are dipped in the etchant bath due to contact with the liquid. If for some reason there is not at least some foreign materials removed by the liquid etchant, it is inherent that at least some foreign materials when the surface upon which they are adhered is etched away. Therefore, it can be considered that the surfaces of the substrates are first cleaned and then eliminated.

Regarding claim 4, Figures 2A-2F of the instant application disclose the steps of: forming a thin film transistor on the lower substrate 18; forming a protective layer 25 on the lower substrate; and forming a pixel electrode 12 on the protective layer to electrically contact the thin film transistor.

Regarding claim 5, the APA discloses the pixel electrode 12 is formed of indium-tin-oxide (page 5, para. [0013] of the instant application).

Regarding claim 6, the APA discloses the protective layer 25 is formed of an acrylic organic compound (page 5, para [0011]).

Regarding claim 7, Figures 2A-2C of the instant application disclose the step of forming the thin film transistor includes: forming a gate electrode 15 on the lower substrate 18; forming a gate insulating film 19 on the lower substrate to cover the gate electrode; forming an active layer

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21 on the gate insulating film; and forming a source electrode 13 and a drain electrode 11 on the active layer.

Regarding claim 8, Figure 2C of the instant application discloses the source electrode 13 and drain electrode 11 contact the gate insulating film.

Regarding claim 9, Figure 2F of the instant application discloses the pixel electrode 12 contacts parallel and inclined surfaces of the drain electrode 11.

Regarding claim 17, Figures 2D-2F of the instant application disclose the steps of: forming a protective layer 25 on the lower substrate; and forming a pixel electrode 12 on the protective layer to electrically contact the drain electrode 11.

Regarding claim 18, the APA discloses the pixel electrode 12 is formed of indium-tin-oxide (page 5, para. [0013] of the instant application).

Regarding claim 19, the APA discloses the protective layer 25 is formed of an acrylic organic compound (page 5, para [0011]).

Claims 1, 3-10, 12-14, and 16-21 are rejected under 35 U.S.C. 103(a) as being unpatentable over the APA in view of Doh (US Pat. 6,675,817).

Regarding claims 1, 3, 10, 12-14, 16, 20, and 21, Figures 2A-F and Figure 3 of this instant application discloses a method of fabricating a liquid crystal display panel, comprising the steps of: preparing an upper substrate 28 and a lower substrate 18; forming a gate electrode 15 on the lower substrate 18; forming a gate insulating film 19 on the lower substrate to cover the gate electrode; forming an active layer 21 on the gate insulating film; and forming a source electrode 13 and a drain electrode 11 on the active layer; and bonding an upper substrate 28 to a

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lower substrate 18. Figure 3 of the APA also discloses foreign materials 25A formed on the lower substrate during the preparing of the lower substrate. The difference between the APA and the claimed invention is the steps of cleaning the exposed surfaces of the bonded upper and lower substrates to remove the foreign materials and simultaneously eliminating/removing the cleaned exposed surfaces of the bonded upper and lower substrates. Doh discloses a method of removing impurities from a substrate 219 (col. 4, lines 13-18). Doh also discloses uniformly reducing the thickness (eliminating exposed surfaces) of the glass substrate by immersing in a liquid etchant bath (col. 4, lines 39-44). It can be considered that the impurities are removed prior to the step of eliminating exposed surfaces since the removal/etching process continues after the removal of at least some of the impurities. In view of such teaching, it would have been obvious to the ordinary artisan at the time the invention was made to modify the invention of the APA by using the cleaning and etching process of Doh for the purpose of obtaining a uniform thickness and a flat surface (col. 4, lines 42-44).

Regarding claim 4, Figures 2A-2F of the instant application disclose the steps of: forming a thin film transistor on the lower substrate 18; forming a protective layer 25 on the lower substrate; and forming a pixel electrode 12 on the protective layer to electrically contact the thin film transistor.

Regarding claim 5, the APA discloses the pixel electrode 12 is formed of indium-tin-oxide (page 5, para. [0013] of the instant application).

Regarding claim 6, the APA discloses the protective layer 25 is formed of an acrylic organic compound (page 5, para [0011]).

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Regarding claim 7, Figures 2A-2C of the instant application disclose the step of forming the thin film transistor includes: forming a gate electrode 15 on the lower substrate 18; forming a gate insulating film 19 on the lower substrate to cover the gate electrode; forming an active layer 21 on the gate insulating film; and forming a source electrode 13 and a drain electrode 11 on the active layer.

Regarding claim 8, Figure 2C of the instant application discloses the source electrode 13 and drain electrode 11 contact the gate insulating film.

Regarding claim 9, Figure 2F of the instant application discloses the pixel electrode 12 contacts parallel and inclined surfaces of the drain electrode 11.

Regarding claim 17, Figures 2D-2F of the instant application disclose the steps of: forming a protective layer 25 on the lower substrate; and forming a pixel electrode 12 on the protective layer to electrically contact the drain electrode 11.

Regarding claim 18, the APA discloses the pixel electrode 12 is formed of indium-tin-oxide (page 5, para. [0013] of the instant application).

Regarding claim 19, the APA discloses the protective layer 25 is formed of an acrylic organic compound (page 5, para [0011]).

Claims 1, 2, 10, 11, 14, and 15 are rejected under 35 U.S.C. 103(a) as being unpatentable over the APA in view of Yoshida et al. (US Pat. 6,508,990, hereinafter Yoshida).

Regarding claims 1, 2, 10, 11, 14, and 15, Figures 2A-F and Figure 3 of this instant application discloses a method of fabricating a liquid crystal display panel, comprising the steps



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of: preparing an upper substrate 28 and a lower substrate 18; forming a gate electrode 15 on the lower substrate 18; forming a gate insulating film 19 on the lower substrate to cover the gate electrode; forming an active layer 21 on the gate insulating film; and forming a source electrode 13 and a drain electrode 11 on the active layer; and bonding an upper substrate 28 to a lower substrate 18. Figure 3 of the APA also discloses foreign materials 25A formed on the lower substrate during the preparing of the lower substrate. The difference between the APA and the claimed invention is the steps of cleaning the exposed surfaces of the bonded upper and lower substrates to remove the foreign materials and simultaneously eliminating/removing the cleaned exposed surfaces of the bonded upper and lower substrates. Figure 10 of Yoshida discloses using a plasma etch (dry-etch) to remove organic contaminants from the surface of a substrate 12 prior to subsequent processing (col. 17, lines 3-11). In view of such teaching, it would have been obvious to the ordinary artisan at the time the invention was made to modify the invention of the APA by using a plasma etch (dry-etch) process to remove foreign materials from the surface of the substrate before eliminating the exposed surfaces. The ordinary artisan would have been motivated to modify the APA in the manner described above since it is well known to remove any impurities from a surface to ensure the impurities do not interfere with any subsequent process steps. Note that if the surface of the substrate 18 is cleaned as proposed by the above combination, the etching step disclosed by the APA (paragraph [0015] of the instant specification) will simultaneously eliminate the cleaned exposed surfaces of the bonded upper and lower substrates.

***Response to Arguments***

Applicant's arguments with respect to claims 1-21 have been considered but are moot in view of the new ground(s) of rejection.

***Conclusion***

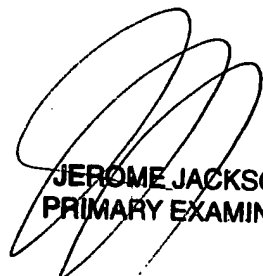
Any inquiry concerning this communication or earlier communications from the examiner should be directed to Matthew C. Landau whose telephone number is (571) 272-1731.

The examiner can normally be reached from 8:30 AM - 5:30 PM. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas can be reached on (571) 272-1664. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 872-9306 for regular communications and (703) 872-9306 for After Final communications.

Matthew C. Landau

Examiner

March 30, 2005

  
JEROME JACKSON  
PRIMARY EXAMINER